



## Voidless Hermetically Sealed Unidirectional Transient Voltage Suppressors

Qualified per MIL-PRF-19500/551

*Qualified Levels:  
JAN, JANTX, and  
JANTXV*

### DESCRIPTION

This surface mount series of 500 watt voidless hermetically sealed unidirectional Transient Voltage Suppressors (TVS) are military qualified to MIL-PRF-19500/551 and are ideal for high-reliability applications where a failure cannot be tolerated. Working peak “standoff” voltages are available from 5.0 to 51.6 volts. They are very robust, using a hard glass casing and internal Category 1 metallurgical bonds. These devices are also available in axial-leaded packages for thru-hole mounting.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- Surface mount equivalent of JEDEC registered 1N6461 thru 1N6468 series.
- Available as 500 watt peak pulse power ( $P_{PP}$ ).
- Working peak “standoff” voltage ( $V_{WM}$ ) from 5.0 to 51.6 volt.
- High surge current and peak pulse power provides transient voltage protection for sensitive circuits.
- Triple-layer passivation.
- Internal “Category 1” metallurgical bonds.
- Voidless hermetically sealed glass package.
- JAN, JANTX, and JANTXV qualifications available per MIL-PRF-19500/551. Other screening in reference to MIL-PRF-19500 is also available.  
(See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

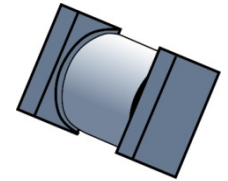
### APPLICATIONS / BENEFITS

- Military and other high-reliability applications.
- Extremely robust construction.
- ESD and EFT protection per IEC61000-4-2 and IEC61000-4-4 respectively.
- Protection from secondary effects of lightning per select levels in IEC61000-4-5.
- Square-end-cap terminals for easy placement.
- Nonsensitive to ESD per MIL-STD-750 method 1020.
- Inherently radiation hard as described in Microsemi “[MicroNote 050](#)”.

### MAXIMUM RATINGS @ 25 °C


Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	$T_J$ and $T_{STG}$	-55 to +175	°C
Thermal Resistance, Junction to Endcap	$R_{\theta JEC}$	20	°C/W
Forward Surge Current @ 8.3 ms half-sine	$I_{FSM}$	80	A
Forward Voltage @ 1 Amp	$V_F$	1.5	V
Peak Pulse Power @ 10/1000 $\mu$ s	$P_{PP}$	500	W
Reverse Power Dissipation <sup>(1)</sup>	$P_R$	2.5	W
Solder Temperature @ 10 s		260	°C

**Notes:** 1. Derate at 50 mW/°C (see [figure 4](#)).



**“B” SQ-MELF  
Package**

Also available in:

**“B” Package**  
(axial –leaded)  
 [1N6461 - 1N6468](#)

**MSC – Lawrence**

6 Lake Street,  
Lawrence, MA 01841  
Tel: 1-800-446-1158 or  
(978) 620-2600  
Fax: (978) 689-0803

**MSC – Ireland**

Gort Road Business Park,  
Ennis, Co. Clare, Ireland  
Tel: +353 (0) 65 6840044  
Fax: +353 (0) 65 6822298

**Website:**

[www.microsemi.com](http://www.microsemi.com)

**MECHANICAL and PACKAGING**

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Axial-leads are tin/lead over copper. RoHS compliant matte-tin is available for commercial grade only.
- MARKING: Body paint and part number.
- POLARITY: Cathode band.
- TAPE & REEL option: Standard per EIA-296. Contact factory for quantities.
- WEIGHT: Approximately 750 milligrams.
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**

**JAN 1N6461 US e3**

**Reliability Level**

JAN = JAN Level  
 JANTX = JANTX Level  
 JANTXV = JANTXV Level  
 CDS (reference JANS)  
 Blank = commercial

**JEDEC type number**

See [Electrical Characteristics](#) table

**RoHS Compliance**

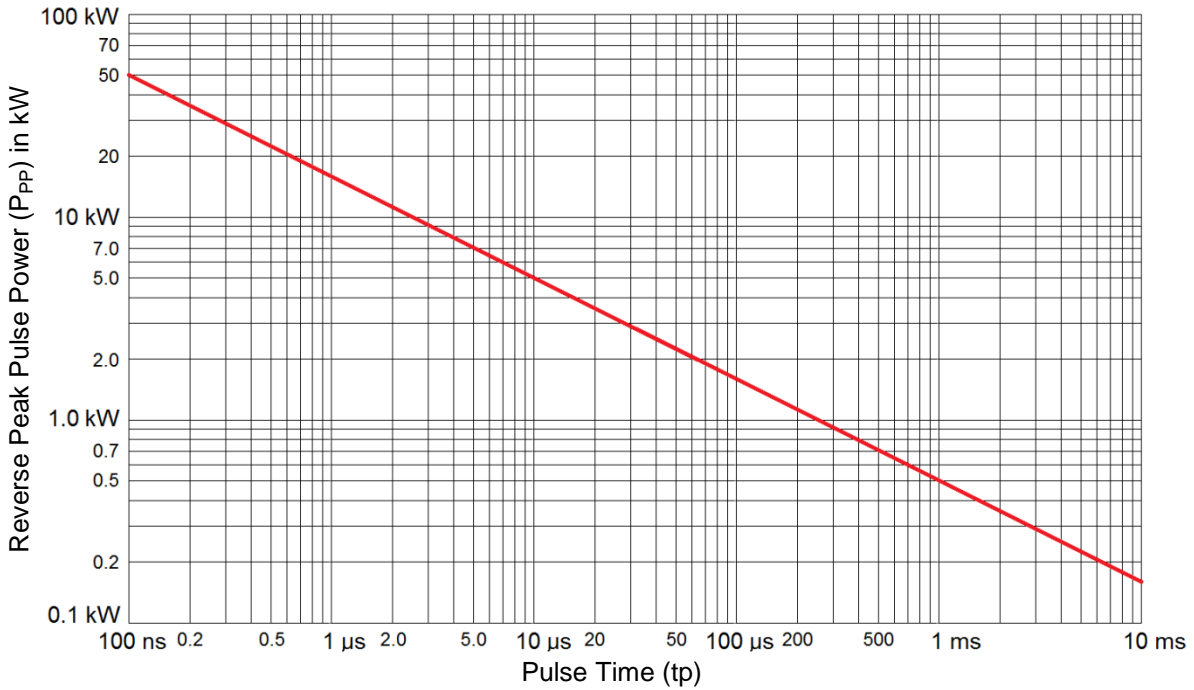
e3 = RoHS compliant ([available on commercial grade only](#))  
 Blank = non-RoHS compliant

**MELF Package**
**SYMBOLS & DEFINITIONS**

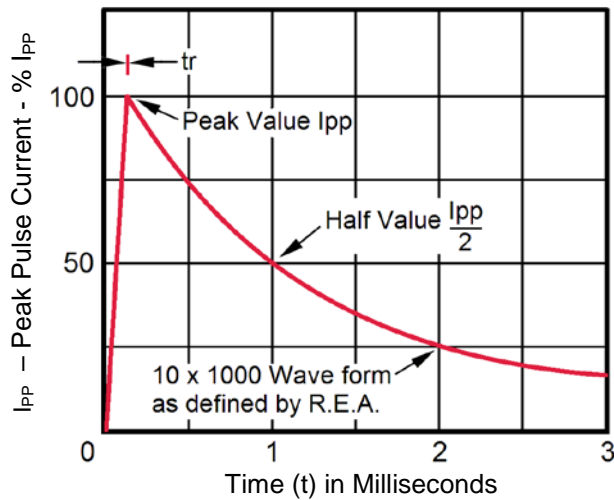
Symbol	Definition
$\alpha_{V(BR)}$	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by the change in temperature expressed in %/°C or mV/°C.
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current $I_{(BR)}$ in the breakdown region.
$V_{WM}$	Rated working standoff voltage: The maximum-rated value of dc or repetitive peak positive cathode-to-anode voltage that may be continuously applied over the standard operating temperature.
$I_D$	Standby Current: The current through the device at rated stand-off voltage.
$I_{PP}$	Peak Impulse Current: The maximum rated random recurring peak impulse current or nonrepetitive peak impulse current that may be applied to a device. A random recurring or nonrepetitive transient current is usually due to an external cause, and it is assumed that its effect will have completely disappeared before the next transient arrives.
$V_C$	Clamping Voltage: The voltage across the device in a region of low differential resistance during the application of an impulse current ( $I_{PP}$ ) for a specified waveform.
$P_{PP}$	Peak Pulse Power. The rated random recurring peak impulse power or rated nonrepetitive peak impulse power. The impulse power is the maximum-rated value of the product of $I_{PP}$ and $V_C$ .

**ELECTRICAL CHARACTERISTICS**

TYPE	MINIMUM BREAK DOWN VOLTAGE $V_{(BR)}$ @ $I_{(BR)}$	BREAKDOWN CURRENT $I_{(BR)}$	RATED WORKING STANDOFF VOLTAGE $V_{WM}$	MAXIMUM STANDBY CURRENT $I_D$ @ $V_{RWM}$	MAXIMUM CLAMPING VOLTAGE $V_C$ @ 10/1000 $\mu s$	MAXIMUM PEAK IMPULSE CURRENT $I_{PP}$		MAXIMUM TEMP. COEF. OF $\alpha V_{(BR)}$
						@ 8/20 $\mu s$	@ 10/1000 $\mu s$	
	Volts	mA	V (pk)	$\mu A$	V (pk)	A (pk)	A (pk)	%/°C
1N6461US	5.6	25	5	3000	9.0	315	56	-0.03, +0.045
1N6462US	6.5	20	6	2500	11.0	258	46	+0.060
1N6463US	13.6	5	12	500	22.6	125	22	+0.085
1N6464US	16.4	5	15	500	26.5	107	19	+0.085
1N6465US	27.0	2	24	50	41.4	69	12	+0.096
1N6466US	33.0	1	30.5	3	47.5	63	11	+0.098
1N6467US	43.7	1	40.3	2	63.5	45	8	+0.101
1N6468US	54.0	1	51.6	2	78.5	35	6	+0.103

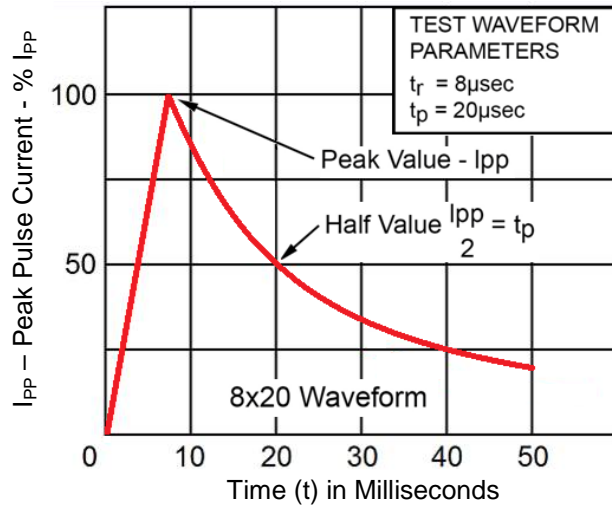
**GRAPHS**


**FIGURE 1**  
Peak Pulse Power vs Pulse Time

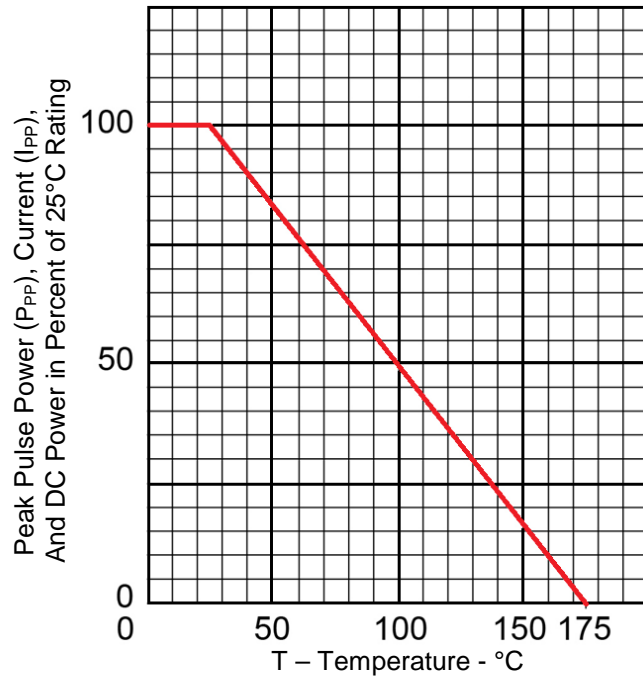


**FIGURE 2**  
10/1000 μs Current Impulse Waveform

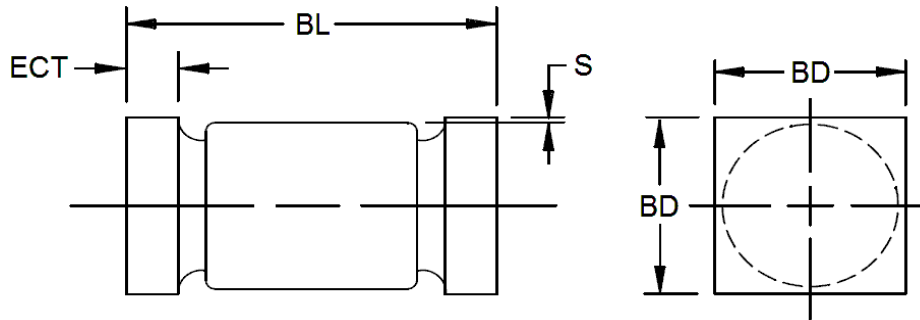
**GRAPHS**



**FIGURE 3**  
8/20  $\mu\text{s}$  Current Impulse Waveform



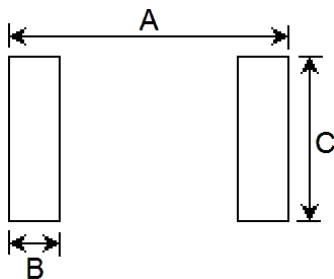
**FIGURE 4**  
Derating Curve

**PACKAGE DIMENSIONS**


	Inch		Millimeters	
	Min	Max	Min	Max
<b>BD</b>	0.137	0.148	3.48	3.76
<b>BL</b>	0.200	0.225	5.08	5.72
<b>ECT</b>	0.019	0.028	0.48	0.71
<b>S</b>	0.003	---	0.08	---

**NOTES:**

1. Dimensions are in inches.
2. Millimeter equivalents are given for information only.
3. Referencing to dimension S, minimum clearance of glass body to mounting surface on all orientations.
4. Dimensions are pre-solder dip.
5. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi$ x symbology.

**PAD LAYOUT**


	INCH	MILLIMETERS
<b>A</b>	0.288	7.32
<b>B</b>	0.070	1.78
<b>C</b>	0.155	3.94

**Note:** If mounting requires adhesive separate from the solder, an additional 0.080 inch diameter contact may be placed in the center between the pads as an optional spot for cement.

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